

ABSTRACT OF THE DISCLOSURE

A microelectronic product and a method for fabricating the same each provide a capacitor formed interposed between a first dielectric layer and a second dielectric layer formed over a substrate having a first contact region and a second contact region exposed therein. The capacitor is also connected to a first conductor stud that penetrates the first dielectric layer and contacts the first contact region and a second conductor stud that penetrates the second dielectric layer. A contiguous conductor interconnect and conductor stud layer is formed within a dual damascene aperture through the second dielectric layer and the first dielectric layer and contacting the second contact region. An etch stop layer employed when forming a trench within the dual damascene aperture also passivates a capacitor sidewall.